

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	887	(semiconductor near3 laser) and substrate and active and ((protect\$4 or shad\$4 or insulat\$4) with vapor) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 09:43
L1	8268	(semiconductor near3 laser) and substrate and active and (protect\$4 or shad\$4 or insulat\$4) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 09:43
L4	144	(semiconductor near3 laser) and (substrate and active) and ((protect\$4 or shad\$4 or insulat\$4) with oxide with vapor) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 09:45
L7	0	5 and 6	US-PGPUB; USPAT	AND	ON	2006/03/31 10:29
L5	231	372/49.01.ccls.	US-PGPUB; USPAT	AND	ON	2006/03/31 10:32
L9	307	438/29.ccls. and (oxide near3 (layer or region or medium or film))	US-PGPUB; USPAT	AND	ON	2006/03/31 10:34
L8	818	438/29.ccls.	US-PGPUB; USPAT	AND	ON	2006/03/31 10:34
L10	965	372/43.01.ccls.	US-PGPUB; USPAT	AND	ON	2006/03/31 10:55
L6	75	372/46.013.ccls.	US-PGPUB; USPAT	AND	ON	2006/03/31 10:55
L11	84	372/46.012.ccls.	US-PGPUB; USPAT	AND	ON	2006/03/31 10:56
L3	13	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4) with oxide with vapor) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 11:05
L12	34	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and (oxide with vapor) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 11:06
L14	0	13 not 12	US-PGPUB; USPAT	AND	ON	2006/03/31 11:13
L13	24	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((oxide near3 (layer or region or medium or film)) with vapor) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 11:13

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L15	0	((semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or (Al near3 "2" near3 O) or (titanium near2 oxide) or (Ti near3 O near3 "2") or (silicon near3 oxide) or (SiO"2")) and (electrode near2 (gold or Au)) and (Si near1 (layer or region or film or medium)) and (electrode with thick\$4)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 11:28
L16	7	((semiconductor near3 laser) and substrate and active and ((protect\$4 or shad\$4 or insulat\$4) with vapor) and electrode).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 11:29
L17	1	((semiconductor near3 laser) and substrate and active and ((protect\$4 or shad\$4 or insulat\$4) with vapor) same electrode).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2006/03/31 11:29
L18	1	((semiconductor near3 laser) and substrate and active and ((protect\$4 or shad\$4 or insulat\$4) with vapor) same electrode).clm.	US-PGPUB	AND	ON	2006/03/31 11:29